

# SANYO Semiconductors

## DATA SHEET

## N-Channel Silicon MOSFET EFC4611—General-Purpose Switching Device **Applications**

## **Features**

- 2.5V drive
- · Best suited for LiB charging and discharging switch
- · Common-drain type

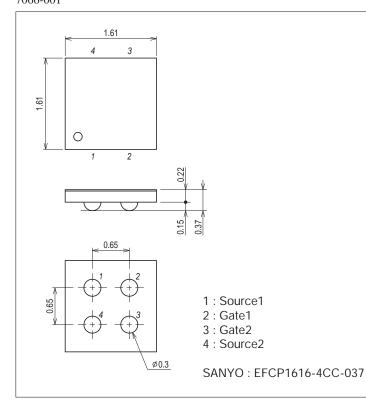
## **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	VSSS		24	V
Gate-to-Source Voltage	VGSS		±12	V
Source Current (DC)	IS		6	А
Source Current (Pulse)	ISP	PW≤100μs, duty cycle≤1%	60	А
Total Dissipation	PT	When mounted on ceramic substrate (5000mm <sup>2</sup> x0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Package Dimensions

unit : mm (typ) 7066-001



#### **Product & Package Information** : EFCP

- Package
- JEITA, JEDEC
- Minimum Packing Quantity : 5,000 pcs./reel

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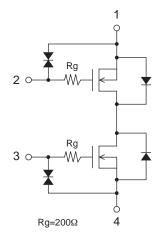
Marking

#### Taping Type : TR

0 TR



### **Electrical Connection**

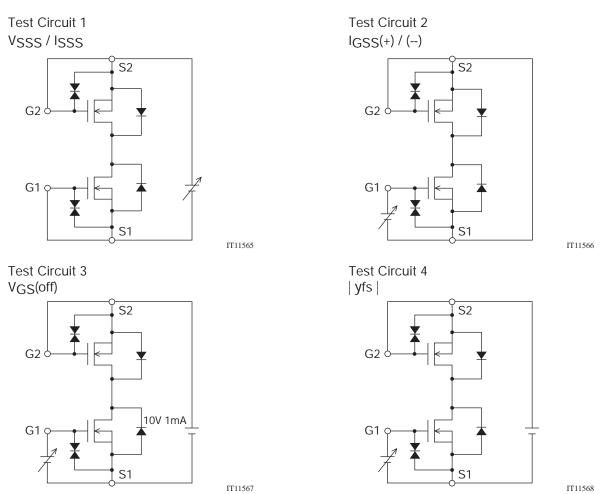


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### Electrical Characteristics at Ta=25°C

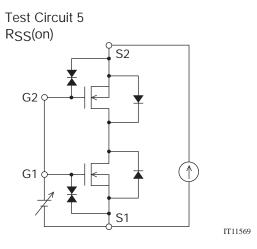
Denemerica	Symbol	Conditions		Ratings			
Parameter				min	typ	max	Unit
Source-to-Source Breakdown Voltage	V(BR)SSS	IS=1mA, VGS=0V	Test Circuit 1	24			V
Zero-Gate Voltage Source Current	ISSS	VSS=20V, VGS=0V	Test Circuit 1			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VSS=0V	Test Circuit 2			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	VSS=10V, IS=1mA	Test Circuit 3	0.5		1.3	V
Forward Transfer Admittance	yfs	VSS=10V, IS=3A	Test Circuit 4		8.9		S
Static Source-to-Source On-State Resistance	R <sub>SS</sub> (on)1	IS=3A, VGS=4.5V	Test Circuit 5	22	30	38	mΩ
	R <sub>SS</sub> (on)2	IS=3A, VGS=4.0V	Test Circuit 5	23	32	41	mΩ
	R <sub>SS</sub> (on)3	IS=3A, VGS=3.1V	Test Circuit 5	26	35	45	mΩ
	RSS(on)4	IS=3A, VGS=2.5V	Test Circuit 5	30.5	41	57.5	mΩ
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.	Test Circuit 7		28		ns
Rise Time	tr	See specified Test Circuit.	Test Circuit 7		205		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.	Test Circuit 7		225		ns
Fall Time	tf	See specified Test Circuit.	Test Circuit 7		250		ns
Total Gate Charge	Qg	VSS=10V, VGS=4.5V, IS=6A			20		nC
Forward Source-to-Source Voltage	V <sub>F(S-S)</sub>	IS=6A, VGS=0V	Test Circuit 6		1	1.2	V

#### Test circuits are example of measuring FET1 side

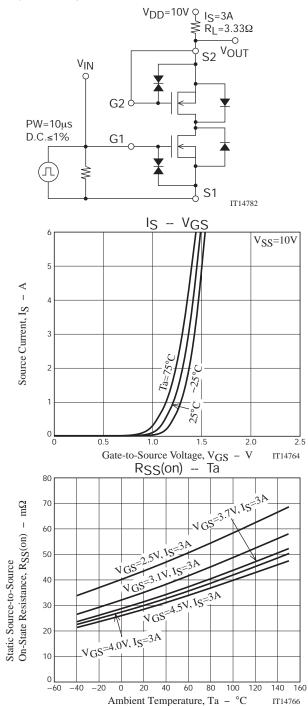


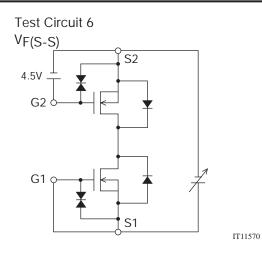
IT11567

\* Note: Connect the mesurement terminal reversely if you want to measure the FET2 side.

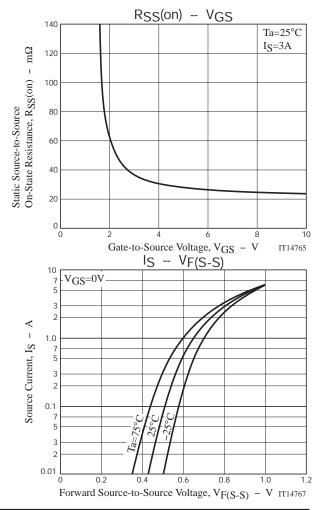


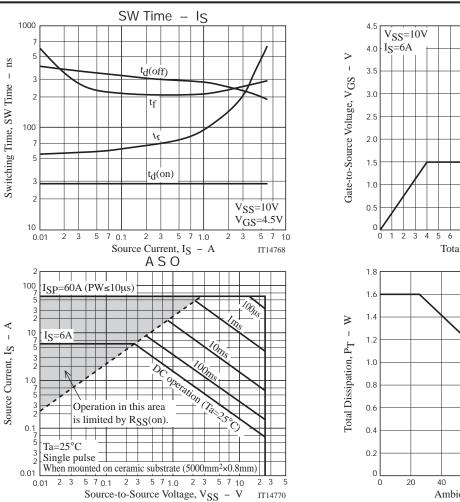
Test Circuit 7  $t_d(on)$ ,  $t_r$ ,  $t_d(off)$ ,  $t_f$ 

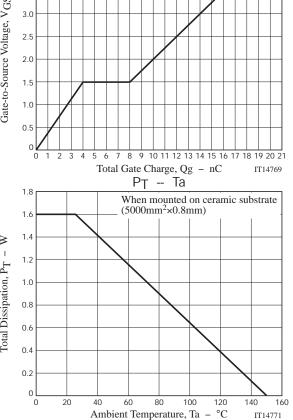




\* Note: Connect the mesurement terminal reversely if you want to measure the FET2 side.







VGS -- Qg

Note on usage : Since the EFC4611 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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